

4Mb Ultra-Low Power Asynchronous CMOS SRAM

256K × 16 bit

Overview

The N04L63W1A is an integrated memory device containing a 4 Mbit Static Random Access Memory organized as 262,144 words by 16 bits. The device is designed and fabricated using ON Semiconductor's advanced CMOS technology to provide both high-speed performance and ultra-low power. The device operates with a single chip enable (\overline{CE}) control and output enable (\overline{OE}) to allow for easy memory expansion. Byte controls $(\overline{UB} \text{ and } \overline{LB})$ allow the upper and lower bytes to be accessed independently. The N04L63W1A is optimal for various applications where low-power is critical such as battery backup and hand-held devices. The device can operate over a very wide temperature range of -40°C to +85°C and is available in JEDEC standard packages compatible with other standard 256Kb x 16 SRAMs.

Features

- Single Wide Power Supply Range 2.3 to 3.6 Volts
- Very low standby current 4.0µA at 3.0V (Typical)
- Very low operating current 2.0mA at 3.0V and 1µs (Typical)
- Very low Page Mode operating current 0.8mA at 3.0V and 1µs (Typical)
- Simple memory control Single Chip Enable (CE) Output Enable (OE) for memory expansion
- Low voltage data retention Vcc = 1.8V
- Very fast output enable access time 25ns OE access time
- Automatic power down to standby mode
- TTL compatible three-state output driver
- Compact space saving BGA package available

Part Number	Package Type	Operating Temperature	Power Supply (Vcc)	Speed Options	Standby Current (I _{SB}), Typical	Operating Current (Icc), Typical
N04L63W1AB	48 - BGA					
N04L63W1AT	44 - TSOP II	4000 1	2 2)/ 2 6)/	70ns @ 2.7V	4 μA	2 mA @ 1MHz
N04L63W1AB2	48 - BGA Green	-40°C to +85°C	2.30 - 3.00	55ns @ 2.7V	4 μΑ	
N04L63W1AT2	44 - TSOP II Green					

56

A₂ NC

CE I/O₀

1/O1 1/O2

I/O₃ V_{CC}

 I/O4
 VSS

 I/O5
 I/O6

 WE
 I/O7

 A11
 NC

Pin Configurations

Product Family

A4 1 0 A3 2 A2 3 A1 4 A0 5 CE 6	PIN ONE	44 A5 43 A6 42 A7 41 OE 40 UB 39 LB	A B	1 LB 1/0 ₈	2 0e UB	3 A ₀ A ₃	4 A ₁ A ₄	5 A2 CE
I/O0 7 I/O1 8	₹	38 I/O15 37 I/O14	С	I/O ₉	I/O ₁₀	A ₅	A ₆	1/0 ₁
I/O2 9 I/O3 10 VCC 11	63W1 OP-II	36 I/O13 35 I/O12 34 VSS	D	\mathbf{v}_{ss}	I/O ₁₁	A ₁₇	A ₇	I/O ₃
VSS 12 1/04 13	4L63 TSO	34 VSS 33 VCC 32 I/O11	Е	v_{cc}	I/O ₁₂	NC	A ₁₆	I/O ₄
I/O5 14 I/O6 15	N04L63W1A TSOP-II	31 I/O10 30 I/O9	F	I/O ₁₄	I/O ₁₃	A ₁₄	A ₁₅	I/O ₅
1/O7 16 WE 17 A16 18	-	29 I/O8 28 NC	G	I/O ₁₅	NC	A ₁₂	A ₁₃	WE
A16 18 A15 19 A14 20		27 A8 26 A9 25 A10	Н	NC	A ₈	A ₉	A ₁₀	A ₁₁
A13 21 A12 22		24 A11 23 A ₁₇		48		BG 8 n	A (to nm))

Pin Descriptions

Pin Name	Pin Function
A ₀ -A ₁₇	Address Inputs
WE	Write Enable Input
CE	Chip Enable Input
OE	Output Enable Input
LB	Lower Byte Enable Input
UB	Upper Byte Enable Input
I/O ₀ -I/O ₁₅	Data Inputs/Outputs
NC	Not Connected
V _{CC}	Power
V _{SS}	Ground



Functional Description

CE	WE	OE	UB	LB	I/O ₀ - I/O ₁₅ ¹	MODE	POWER
Н	Х	Х	Х	Х	High Z	Standby ²	Standby
L	Х	Х	Н	Н	High Z	Standby ²	Standby
L	L	Х ³	L ¹	L^1	Data In	Write ³	Active
L	Н	L	L^1	L ¹	Data Out	Read	Active
L	Н	Н	L ¹	L ¹	High Z	Active	Active

1. When $\overline{\text{UB}}$ and $\overline{\text{LB}}$ are in select mode (low), I/O₀ - I/O₁₅ are affected as shown. When $\overline{\text{LB}}$ only is in the select mode only I/O₀ - I/O₇ are affected as shown. When $\overline{\text{UB}}$ is in the select mode only I/O₈ - I/O₁₅ are affected as shown.

2. When the device is in standby mode, control inputs (WE, OE, UB, and LB), address inputs and data input/outputs are internally isolated from any external influence and disabled from exerting any influence externally.

3. When $\overline{\text{WE}}$ is invoked, the $\overline{\text{OE}}$ input is internally disabled and has no effect on the circuit.

Capacitance¹

ltem	Symbol	Test Condition	Min	Мах	Unit
Input Capacitance	C _{IN}	V _{IN} = 0V, f = 1 MHz, T _A = 25°C		8	pF
I/O Capacitance	C _{I/O}	V _{IN} = 0V, f = 1 MHz, T _A = 25°C		8	pF

1. These parameters are verified in device characterization and are not 100% tested

Absolute Maximum Ratings¹

Item	Symbol	Rating	Unit
Voltage on any pin relative to V_{SS}	V _{IN,OUT}	–0.3 to V _{CC} +0.3	V
Voltage on V_{CC} Supply Relative to V_{SS}	V _{CC}	–0.3 to 4.5	V
Power Dissipation	PD	500	mW
Storage Temperature	T _{STG}	-40 to 125	°C
Operating Temperature	T _A	-40 to +85	°C
Soldering Temperature and Time	T _{SOLDER}	260 ^o C, 10sec	°C

 Stresses greater than those listed above may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operating section of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

Operating Characteristics (Over Specified Temperature Range)

Item	Symbol	Test Conditions	Min.	Typ ¹	Мах	Unit
Supply Voltage	V _{CC}		2.3	3.0	3.6	V
Data Retention Voltage	V_{DR}	Chip Disabled ²	1.8			V
Input High Voltage	V _{IH}		1.8		V _{CC} +0.3	V
Input Low Voltage	V _{IL}		-0.3		0.6	V
Output High Voltage	V _{OH}	I _{OH} = 0.2mA	V _{CC} -0.2			V
Output Low Voltage	V _{OL}	I _{OL} = -0.2mA			0.2	V
Input Leakage Current	I _{LI}	V _{IN} = 0 to V _{CC}			0.5	μA
Output Leakage Current	I _{LO}	$\overline{OE} = V_{IH}$ or Chip Disabled			0.5	μA
Read/Write Operating Supply Current @ 1 µs Cycle Time ²	I _{CC1}	V_{CC} =3.6 V, V_{IN} = V_{IH} or V_{IL} Chip Enabled, I_{OUT} = 0		2.0	3.0	mA
Read/Write Operating Supply Current @ 70ns Cycle Time ²	I _{CC2}	V_{CC} =3.6 V, V_{IN} = V_{IH} or V_{IL} Chip Enabled, I_{OUT} = 0		10	16.0	mA
Page Mode Operating Supply Current @ 70ns Cycle Time ² (Refer to Power Savings with Page Mode Operation diagram)	I _{CC3}	V _{CC} =3.6 V, V _{IN} =V _{IH} or V _{IL} Chip Enabled, I _{OUT} = 0		4		mA
Read/Write Quiescent Operating Sup- ply Current ³	I _{CC4}	V_{CC} =3.6 V, V_{IN} = V_{IH} or V_{IL} Chip Enabled, I_{OUT} = 0, f = 0			3.0	mA
Maximum Standby Current ³	I _{SB1}	$V_{IN} = V_{CC} \text{ or } 0V$ Chip Disabled $t_A = 85^{\circ}C, VCC = 3.6 V$		4.0	20	μA
Maximum Data Retention Current ³	I _{DR}	V_{CC} = 1.8V, V_{IN} = V_{CC} or 0 Chip Disabled, t_A = 85°C			10	μA

1. Typical values are measured at Vcc=Vcc Typ., $T_A \text{=} 25^\circ\text{C}$ and are not 100% tested.

2. This parameter is specified with the outputs disabled to avoid external loading effects. The user must add current required to drive output capacitance expected in the actual system.

3. This device assumes a standby mode if the chip is disabled (CE high or UB and LB high). In order to achieve low standby current all inputs must be within 0.2 volts of either VCC or VSS

Power Savin	gs with Page Mode (Dperation (WE	= V _{IH})		
Page Addre	ss (A4 - A17)	Оре	n page		X
Word Addre	ess (A0 - A3) Wor	rd 1 Vord 2		Word 16	
CE					
ŌĒ					
$\overline{LB}, \overline{UB}$					

Note: Page mode operation is a method of addressing the SRAM to save operating current. The internal organization of the SRAM is optimized to allow this unique operating mode to be used as a valuable power saving feature.

The only thing that needs to be done is to address the SRAM in a manner that the internal page is left open and 16-bit words of data are read from the open page. By treating addresses A0-A3 as the least significant bits and addressing the 16 words within the open page, power is reduced to the page mode value which is considerably lower than standard operating currents for low power SRAMs.

Timing Test Conditions

Item	
Input Pulse Level	0.1V _{CC} to 0.9 V _{CC}
Input Rise and Fall Time	5ns
Input and Output Timing Reference Levels	0.5 V _{CC}
Output Load	CL = 30pF
Operating Temperature	-40 to +85 °C

Timing

			-7	70		-4	55	
Item	Symbol	2.3 - 2	2.65 V	2.7 -	3.6 V	2.7 -	3.6 V	Units
		Min.	Max.	Min.	Max.	Min.	Max.	
Read Cycle Time	t _{RC}	85		70		55		ns
Address Access Time	t _{AA}		85		70		55	ns
Chip Enable to Valid Output	t _{CO}		85		70		55	ns
Output Enable to Valid Output	t _{OE}		30		25		25	ns
Byte Select to Valid Output	t _{LB} , t _{UB}		85		70		55	ns
Chip Enable to Low-Z output	t _{LZ}	10		10		10		ns
Output Enable to Low-Z Output	t _{OLZ}	5		5		5		ns
Byte Select to Low-Z Output	t _{BZ}	10		10		10		ns
Chip Disable to High-Z Output	t _{HZ}	0	20	0	20	0	20	ns
Output Disable to High-Z Output	t _{OHZ}	0	20	0	20	0	20	ns
Byte Select Disable to High-Z Output	t _{BHZ}	0	20	0	20	0	20	ns
Output Hold from Address Change	t _{OH}	10		10		10		ns
Write Cycle Time	t _{WC}	85		70		55		ns
Chip Enable to End of Write	t _{CW}	50		50		45		ns
Address Valid to End of Write	t _{AW}	50		50		45		ns
Byte Select to End of Write	t _{BW}	50		50		45		ns
Write Pulse Width	t _{WP}	40		40		40		ns
Address Setup Time	t _{AS}	0		0		0		ns
Write Recovery Time	t _{WR}	0		0		0		ns
Write to High-Z Output	t _{WHZ}		20		20		20	ns
Data to Write Time Overlap	t _{DW}	40		40		40		ns
Data Hold from Write Time	t _{DH}	0		0		0		ns
End Write to Low-Z Output	t _{OW}	5		5		5		ns



Timing Waveform of Read Cycle ($\overline{WE} = V_{IH}$)



Data In

Data Out





t_{WHZ}

t_{LZ} ◀►

t_{DW}

Data Valid

High-Z

t_{DH}



Note:

- 1. All dimensions in inches (Millimeters)
- 2. Package dimensions exclude molding flash



Dimensions (mm)

D	Е		BALL MATRIX			
D		SD	SD SE J		к	TYPE
6±0.10	8±0.10	0.375	0.375	1.125	1.375	FULL

Ordering Information

Part Number	Package	Shipping Method
N04L63W1AT7I	Leaded 44-TSOP II	Tray
N04L63W1AT27I	Green 44-TSOP II (RoHS Compliant)	Tray
N04L63W1AB7I	Leaded 48-BGA	Tray
N04L63W1AB27I	Green 48-BGA (RoHS Compliant)	Tray
N04L63W1AT7IT	Leaded 44-TSOP II	Tape & Reel
N04L63W1AT27IT	Green 44-TSOP II (RoHS Compliant)	Tape & Reel
N04L63W1AB7IT	Leaded 48-BGA	Tape & Reel
N04L63W1AB27IT	Green 48-BGA (RoHS Compliant)	Tape & Reel

Please contact factory for 55ns speed grade

Revision History

Revision #	Date	Change Description
А	Jan. 2001	Initial Preliminary Release
В	Mar. 2001	Eliminated CE2 from BGA pinout, other minor errata
С	May. 2001	Revised TSOP Pacakge diagram
D	June. 2001	Revised BGA Package Dimensions table
E	Dec. 2001	Part number change from EM256L16, modified Overview and Features, added Page Mode Operation diagram, revised Operating Characteristics table, Package diagram, Functional Description table and Ordering Information diagram
F	Nov. 2002	Replaced Isb and Icc on Product Family table with typical values
G	February 2003	Added 55ns sort
Н	August 2004	Removed 55ns sort
I	Oct 2004	Added Pb-Free and Green Package Option
J	Nov. 2005	Removed Pb-Free Pkg, added Green Pkg and RoHS Compliant
К	September 2006	Converted to AMI Semiconductor
L	October 2007	Added 55ns performance sort
13	July 2008	Converted to ON Semiconductor and new part numbers

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